

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

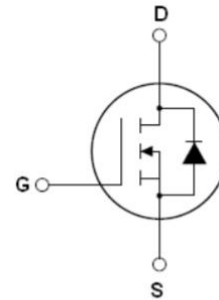
Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

$V_{DS\ min@T_{jmax}}$	550	V
$R_{DS(ON)TYP.}$	150	m Ω
I_D	17	A
Q_g	22	nC



Schematic diagram

✧ **Intrinsic fast-recovery body diode**

Package Marking And Ordering Information

Device	Device Package	Marking
NCE50NF180F	TO-220F-3L	NCE50NF180F



GDS
TO-220F

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	500	V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$), DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	17	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	11.9	A
Pulsed drain current (Note 1)	$I_{DM(pulse)}$	51	A
Maximum Power Dissipation($T_c=25^\circ\text{C}$)	P_D	33.8	W
Derate above 25°C		0.23	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	62.5	mJ
Single pulse avalanche current (Note 2)	I_{AS}	5	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.54	mJ
Reverse diode dv/dt , $V_{DS} \leq 400\text{ V}, I_{SD} < I_D$	dv/dt	50	V/ns
Drain Source voltage slope, $V_{DS} \leq 400\text{ V}$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55...+175	$^\circ\text{C}$

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	4.44	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	500			V
Zero Gate Voltage Drain Current($T_c=25^{\circ}\text{C}$)	I_{DSS}	$V_{DS}=500V, V_{GS}=0V$			10	μA
Zero Gate Voltage Drain Current($T_c=125^{\circ}\text{C}$)	I_{DSS}	$V_{DS}=500V, V_{GS}=0V$			200	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 200	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	3		5	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=8.5A$		150	180	m Ω
Dynamic Characteristics						
Gate Resistance	R_g	$F=1\text{MHz}, \text{D-S short}$		18		Ω
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V,$ $F=1\text{MHz}$		1157		pF
Output Capacitance	C_{oss}			52		pF
Reverse Transfer Capacitance	C_{riss}			4.8		pF
Total Gate Charge	Q_g	$V_{DS}=350V, I_D=8.5A,$ $V_{GS}=10V$		22		nC
Gate-Source Charge	Q_{gs}			9.1		nC
Gate-Drain Charge	Q_{gd}			5.1		nC
Gate plateau voltage	V_{gp}			6.6		V
Switching times						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=400V, I_D=8.5A,$ $R_G=4\Omega, V_{GS}=10V$		12		nS
Turn-on Rise Time	t_r			10		nS
Turn-Off Delay Time	$t_{d(off)}$			56		nS
Turn-Off Fall Time	t_f			8		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I_{SD}	$T_c=25^{\circ}\text{C}$			17	A
Pulsed-Source-drain current(Body Diode)	I_{SDM}				51	A
Forward on voltage	V_{SD}	$T_j=25^{\circ}\text{C}, I_{SD}=17A, V_{GS}=0V$		0.9	1.1	V
Reverse Recovery Time	t_{rr}	$T_j=25^{\circ}\text{C}, I_f=8.5A,$ $di/dt=100A/\mu s$		165		nS
Reverse Recovery Charge	Q_{rr}			0.83		μC
Peak reverse recovery current	I_{rrm}			10		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

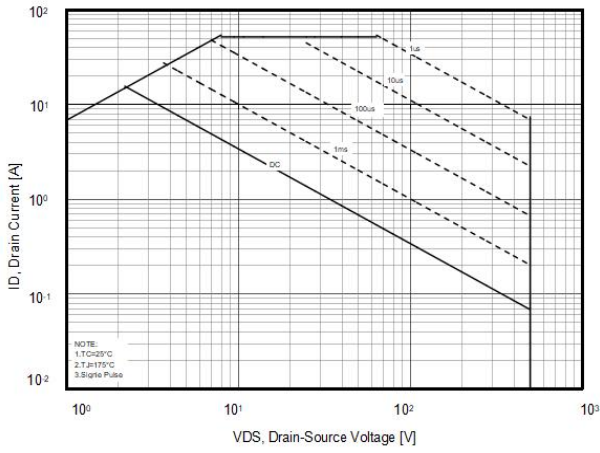


Figure2. Source-Drain Diode Forward Voltage

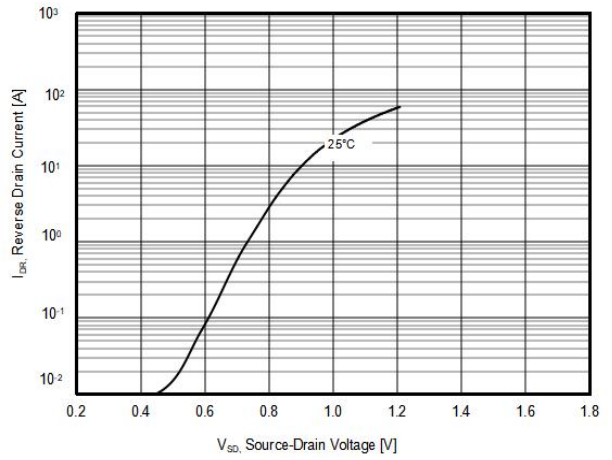


Figure3. Output characteristics

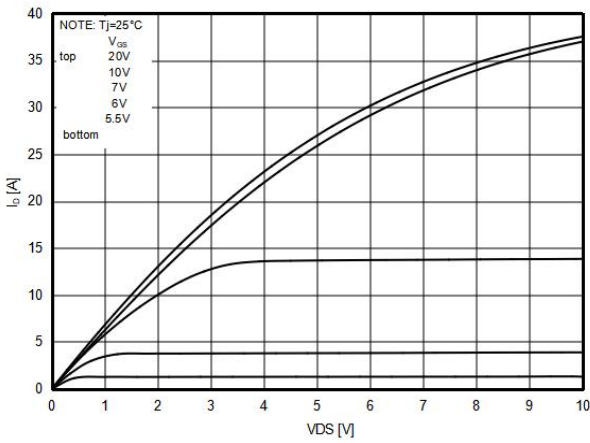


Figure4. Transfer characteristics

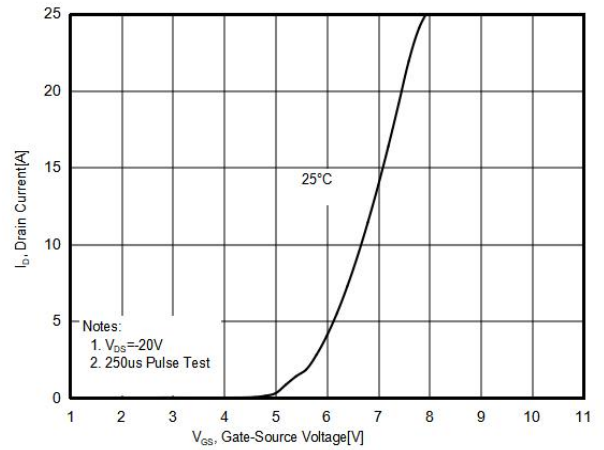


Figure5. Static drain-source on resistance

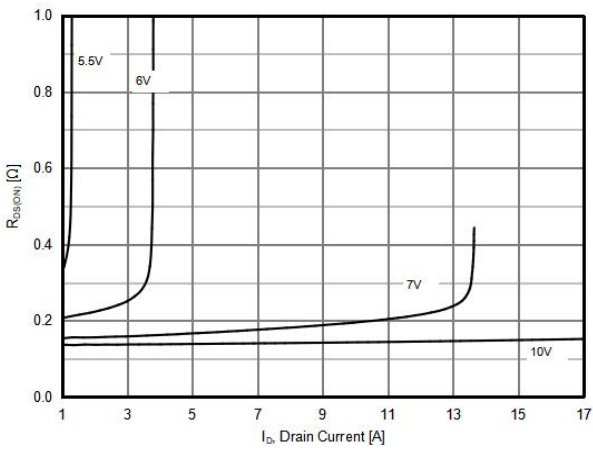


Figure6. R_DS(ON) vs Junction Temperature

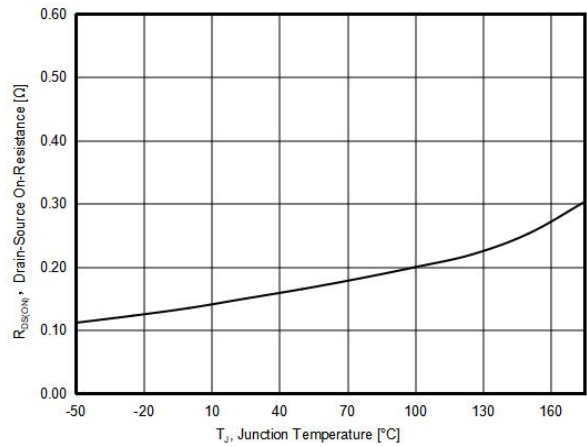


Figure7. BV_{DSS} vs Junction Temperature

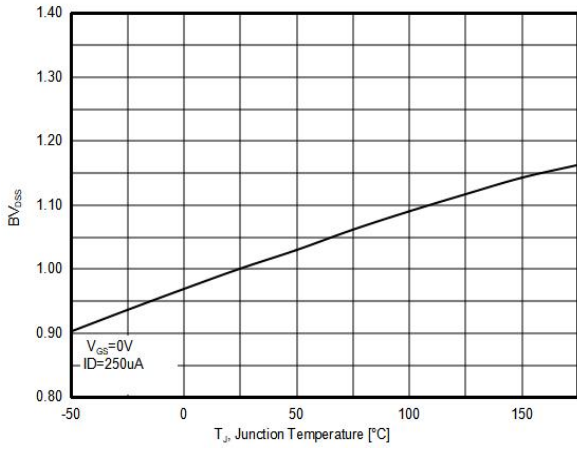


Figure8. Maximum I_D vs Junction Temperature

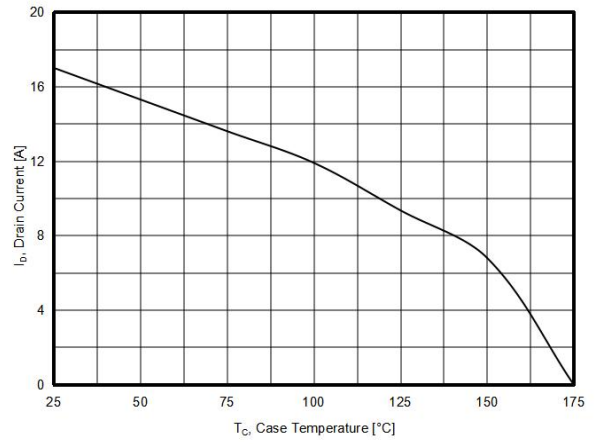


Figure9. Gate charge waveforms

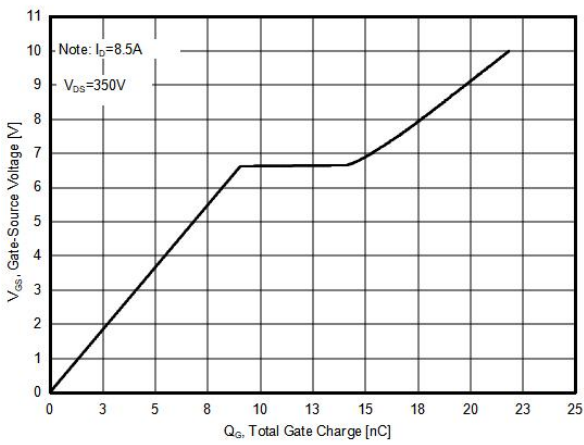
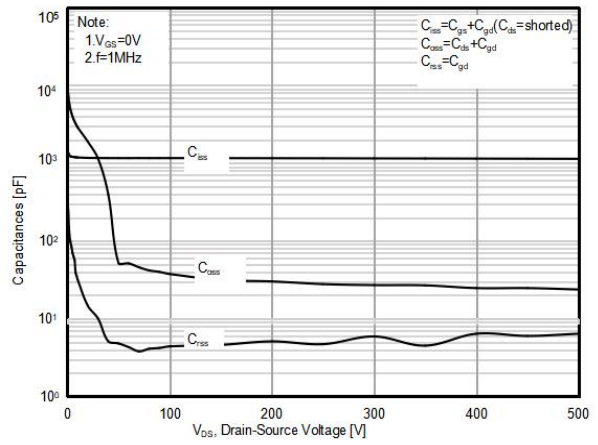


Figure10. Capacitance

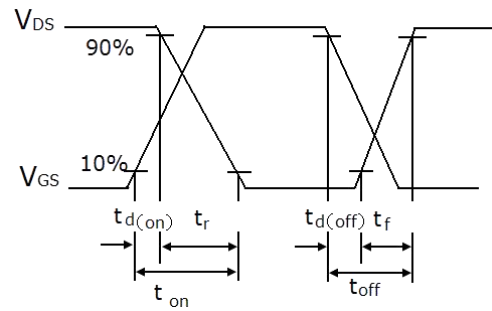


Test circuit

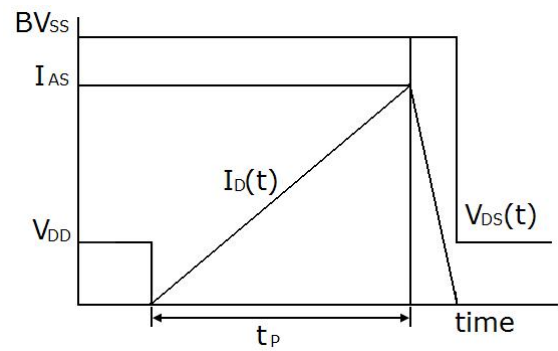
1) Gate charge test circuit & Waveform



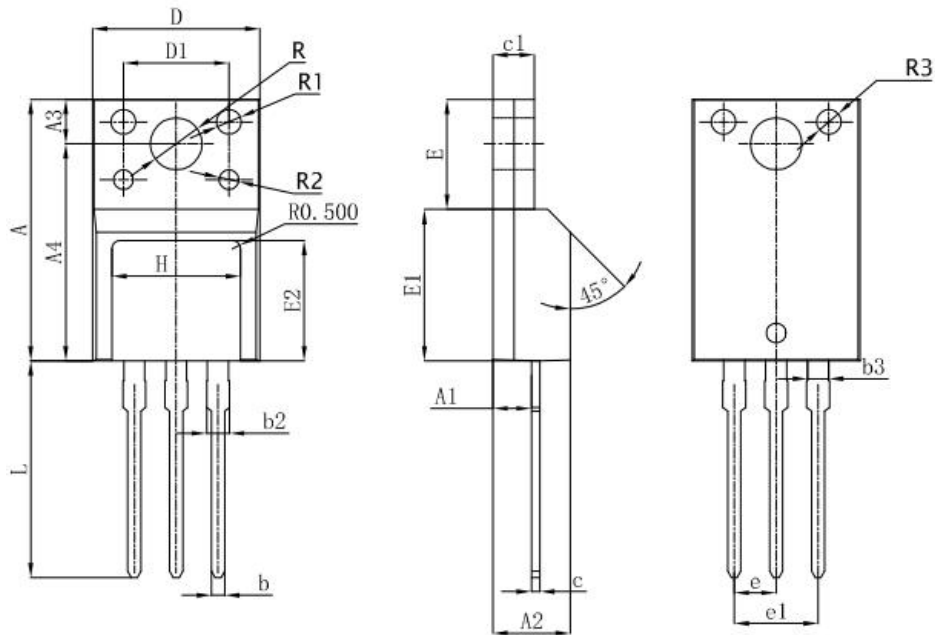
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms

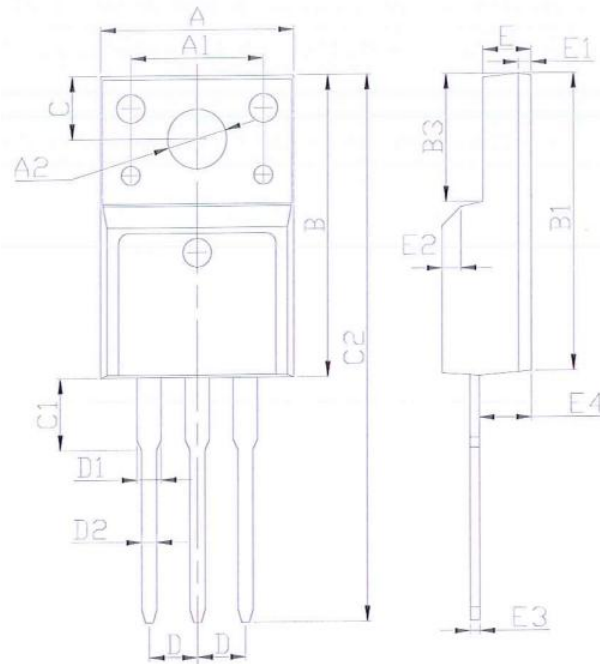


TO-220F-S Package Information



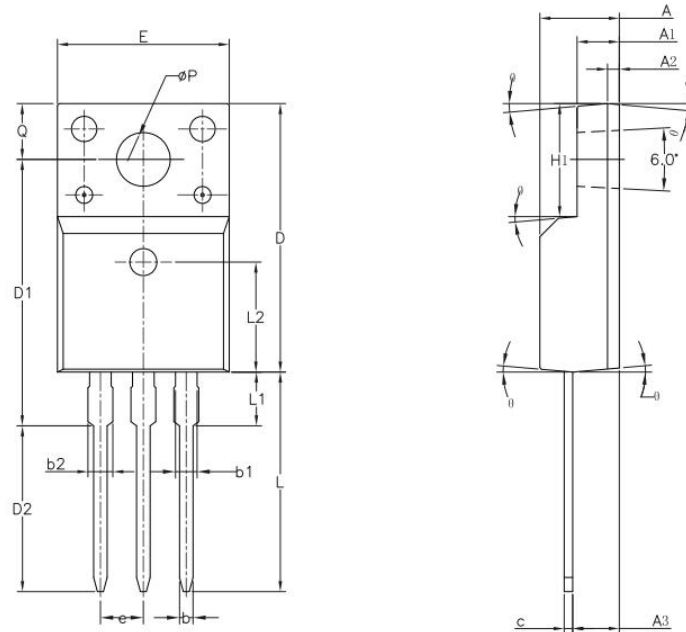
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	15.67	15.87	0.616	0.623
A1	2.15	2.35	0.084	0.092
A2	4.50	4.70	0.177	0.185
A3	3.10	3.50	0.122	0.138
A4	12.27	12.87	0.482	0.506
b	0.77	0.83	0.030	0.033
b2	1.20	1.40	0.047	0.055
b3	1.20 BSC		0.047 REF	
c	0.40	0.60	0.016	0.024
c1	2.44	2.64	0.096	0.104
D	9.86	10.46	0.387	0.411
D1	6.90	7.10	0.271	0.279
E	6.48	6.88	0.255	0.270
E1	8.99	9.39	0.353	0.369
E2	7.10	7.50	0.279	0.295
e	2.54 BSC		0.100 BSC	
e1	5.08 BSC		0.200 BSC	
L	13.14	13.54	0.516	0.532
R	3.10	3.50	0.122	0.138
H	7.60	8.00	0.299	0.314
θ1	4.0°	5.0°	4.00°	5.00°

TO-220F-L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	9.86	10.46	0.387	0.411
A1	6.80	7.20	0.267	0.283
A3	9.40	10.00	0.369	0.393
B	15.40	16.40	0.605	0.644
B1	15.10	16.10	0.593	0.633
B2	4.40	5.00	0.173	0.196
B3	6.40	7.00	0.251	0.275
C	3.05	3.55	0.120	0.139
C1	2.95	3.55	0.116	0.139
C2	28.20	29.20	1.108	1.147
D	2.54 BSC		0.100 BSC	
D1	--	1.47	--	0.058
D2	0.60	1.00	0.024	0.039
E	2.30	2.80	0.090	0.110
E1	0.45	0.95	0.018	0.037
E2	45.0°		45.00°	
E3	0.30	0.70	0.012	0.028
E4	2.45	3.05	0.096	0.120

TO-220F-P Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.83	0.177	0.190
A1	2.34	2.74	0.092	0.108
A2	0.70 REF		0.028 REF	
A3	2.56	2.93	0.101	0.115
b	0.70	0.90	0.028	0.035
b1	1.18	1.38	0.046	0.054
b2	--	1.47	--	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.616	0.631
D1	15.55	15.95	0.611	0.627
D2	9.60	10.00	0.377	0.393
E	9.96	10.36	0.391	0.407
e	2.54 BSC		0.100 BSC	
H1	6.48	6.88	0.255	0.270
L	12.68	13.28	0.498	0.522
L1	--	3.50	--	0.138
L2	6.50 REF		0.255 REF	
∅ P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134
θ1	1.0°	5.0°	1.00°	5.00°

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